2SK4088LS

N-Channel Power MOSFET 650V, 11A, 0.85Ω, TO-220F-3FS

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Features

• ON-resistance $RDS(on)=0.65\Omega$ (typ.)

• Input capacitance Ciss=1000pF (typ.)

• 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	VDSS		650	V
Gate to Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	11	А
	I _{Dpack} *2	Tc=25°C (Our ideal heat dissipation condition)*3	7.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	40	А
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C (Our ideal heat dissipation condition)*3	37	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	Eas		65	mJ
Avalanche Current *5	IAV		11	А

Note :*1 Shows chip capability

*2 Package limited

*3 Our condition is radiation from backside.

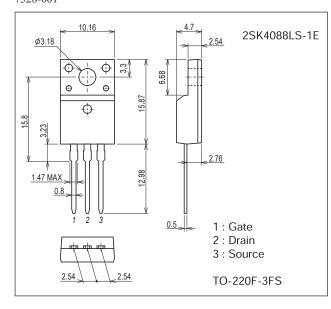
The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium. * $4 V_{DD}=50V, L=1mH, I_{AV}=11A$ (Fig.1)

*5 L≤1mH, single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7528-001

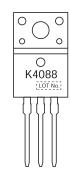


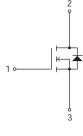
Ordering & Package Information

	0		
Device	Package	Shipping	memo
2SK4088LS-1E	TO-220F-3FS, SC-67	50pcs./tube	Pb-Free

Marking

Electrical Connection





Electrical Characteristics at Ta=25°C

Deventer	Currents and		Ratings			
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	650			V
Zero-Gate Voltage Drain Current	IDSS	VDS=520V, VGS=0V			100	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	3		5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =5.5A	3.3	6.5		S
Static Drain to Source On-State Resistance	R _{DS} (on)	ID=5.5A, VGS=10V		0.65	0.85	Ω
Input Capacitance	Ciss			1000		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		172		рF
Reverse Transfer Capacitance	Crss			36		pF
Turn-ON Delay Time	t _d (on)			24		ns
Rise Time	tr			58		ns
Turn-OFF Delay Time	t _d (off)	- See specified Test Circuit.		117		ns
Fall Time	tf			40		ns
Total Gate Charge	Qg			37.6		nC
Gate to Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =11A		6.8		nC
Gate to Drain "Miller" Charge	Qgd			17.6		nC
Diode Forward Voltage	V _{SD}	IS=11A, VGS=0V		0.9	1.2	V

Fig.1 Unclamped Inductive Switching Test Circuit

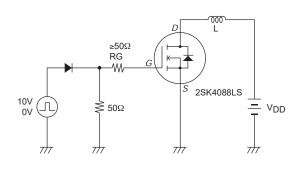
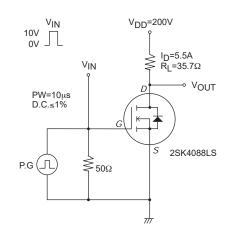
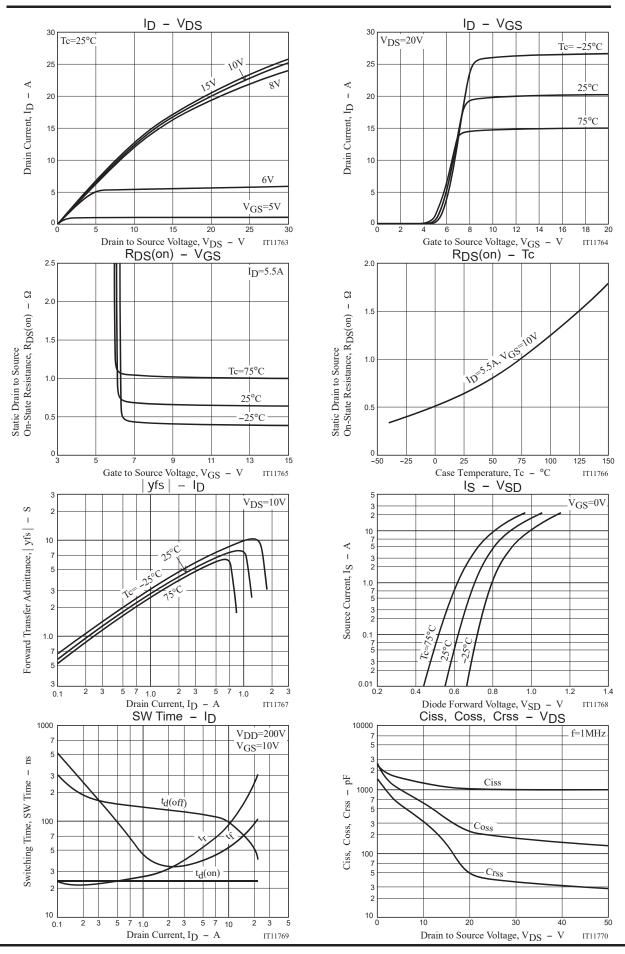
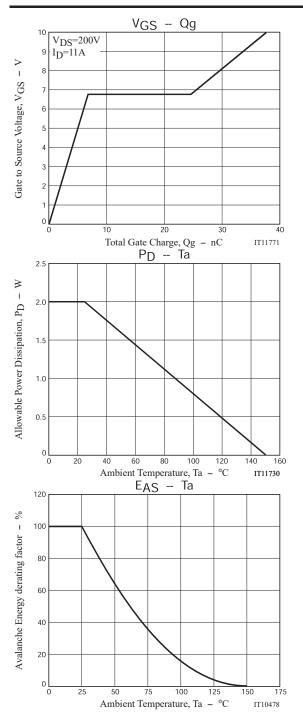


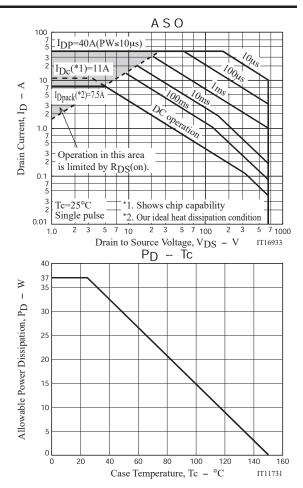
Fig.2 Switching Time Test Circuit





2SK4088LS





Magazine Specification

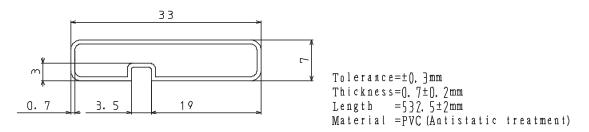
2SK4088LS-1E

1. Packing Format

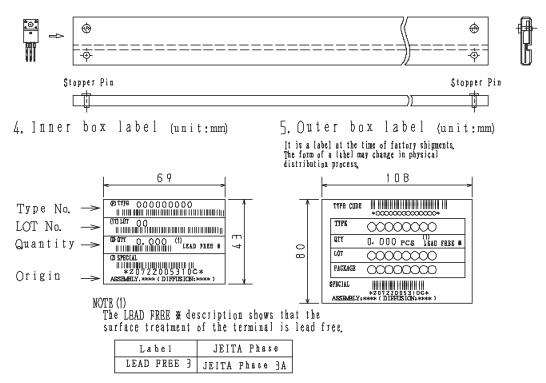
Package Name Magazine Name		Maximum Number of devices contained (pcs)			Packing format		
1111101 11111	Intel and the Hamp		Inner box	Quter bax	Inner BOX	Outer BOX	
TO-220F-3F\$	TO-220F	50	1,000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner baxes contained Dimensions:mm {external} 590×225×178	

2. Magazine dimensions

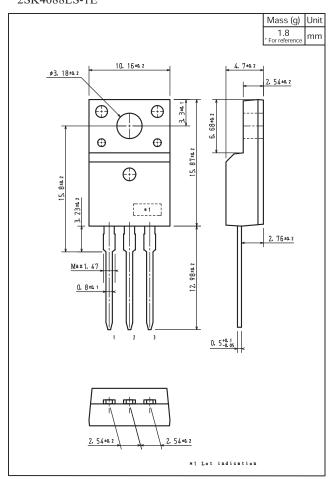
(unit:mm)



3. Storage method to magazine



Outline Drawing 2SK4088LS-1E



Note on usage : Since the 2SK4088LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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